★ Green Device Available
★ Super Low Gate Charge
★ Excellent CdV/dt effect decline
★ Advanced high cell density Trench technology

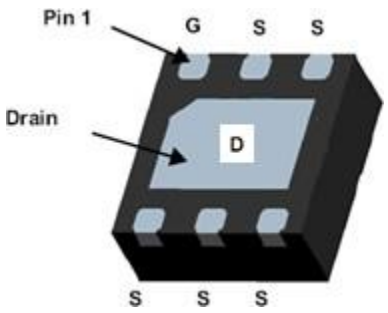
BVDSS	RDSON	ID
-15V	24mΩ	- 7 A

Description

The ZX 415 is the high cell density trenched P-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The ZX 415 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

DFN2X2-6L Pin Configuration



Package Marking and Ordering Information

Product	Package	Marking	Packing	Min Unit Quantity
ZX 415	PDN2*2-6L	*	5000PCS/Reel	5000PCS

Absolute Maximum Ratings (TA=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-16	V
Gate-Source Voltage	V_{GS}	±12	V
Drain Current -Continuous	I_D	-7.0	A
Drain Current -Pulsed (Note 1)	I_{DM}	-15	A
Maximum Power Dissipation	P_D	2.5	W
Operating Junction and Storage Temperature Range	T_J,T_{STG}	-55 To 150	℃

Thermal Characteristic

Thermal Resistance,Junction-to-Ambient (Note 2)	$R_{\theta JA}$	74	℃/W

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-16V,V_{GS}=0V	-	-	-1	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±12V,V_{DS}=0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=-250μA	-0.45	-0.7	-1.0	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=-4.5V, I_D=-4.1A	-	24	45	mΩ
		V_{GS}=-2.5V, I_D=-3A	-	40	60	
Forward Transconductance	g_{FS}	V_{DS}=-5V,I_D=-4.1A	5	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C_{lss}	V_{DS}=-4V,V_{GS}=0V, F=1.0MHz	-	740	-	PF
Output Capacitance	C_{oss}		-	290	-	PF
Reverse Transfer Capacitance	C_{rss}		-	190	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=-4V,I_D=-4.1A , R_L=-1.2Ω,V_{GEN}=-4.5V,R_g=1Ω	-	12	-	nS
Turn-on Rise Time	t_r		-	35	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	30	-	nS
Turn-Off Fall Time	t_f		-	10	-	nS
Total Gate Charge	Q_g	V_{DS}=-4V,I_D=-4.1A,V_{GS}=-4.5V	-	7.8	-	nC
Gate-Source Charge	Q_{gs}		-	1.2	-	nC
Gate-Drain Charge	Q_{gd}		-	1.6	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	V_{GS}=0V,I_S=-4.1A	-	-	-1.2	V
Diode Forward Current (Note 2)	I_S		-	-	-7.1	A

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production

Typical Electrical and Thermal Characteristics

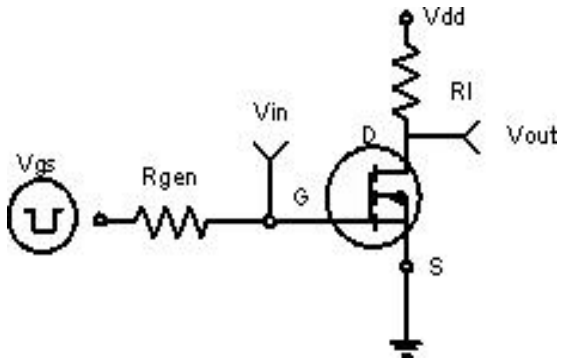


Figure 1:Switching Test Circuit

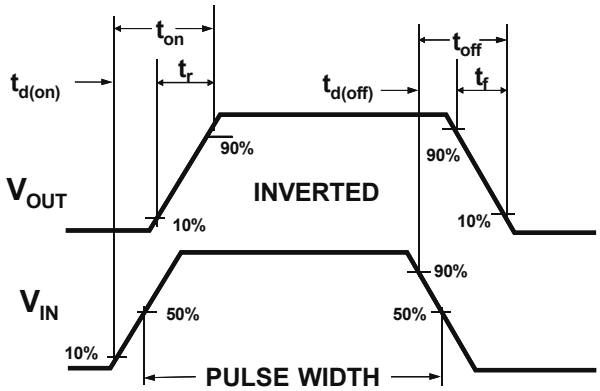
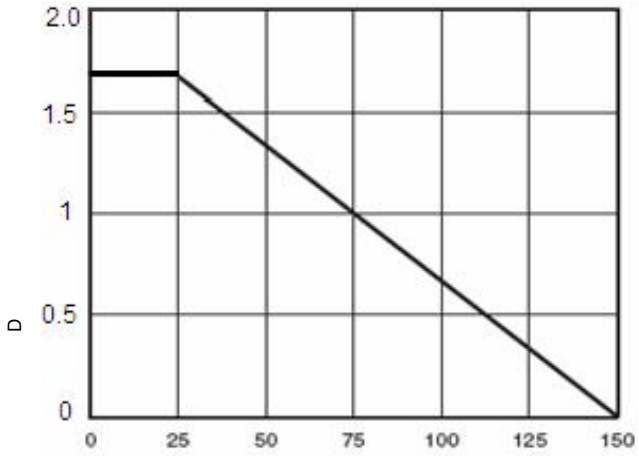
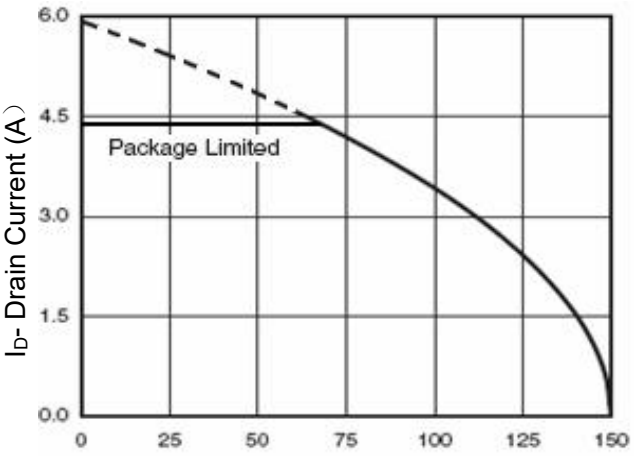


Figure 2:Switching Waveforms



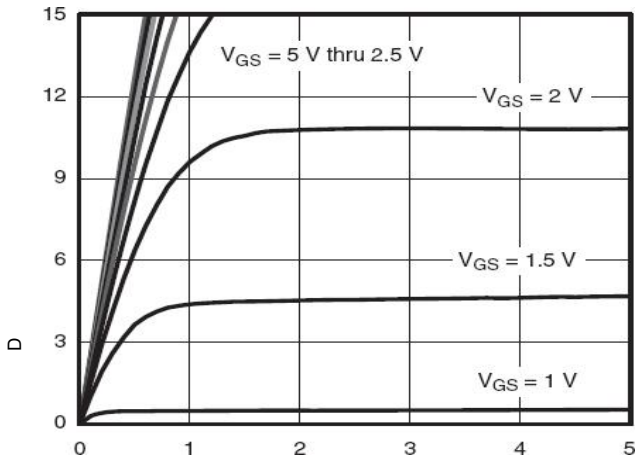
TJ-Junction Temperature(℃)

Figure 3 Power Dissipation



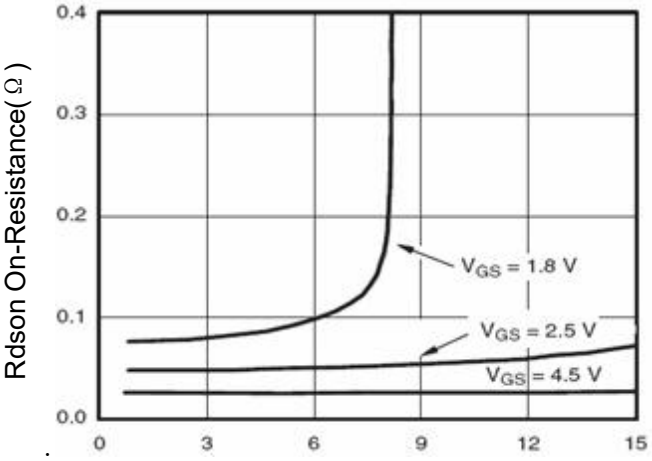
TJ-Junction Temperature(℃)

Figure 4 Drain Current



Vds Drain-Source Voltage (V)

Figure 5 Output Characteristics



ID- Drain Current (A)

Figure 6 Drain-Source On-Resistance

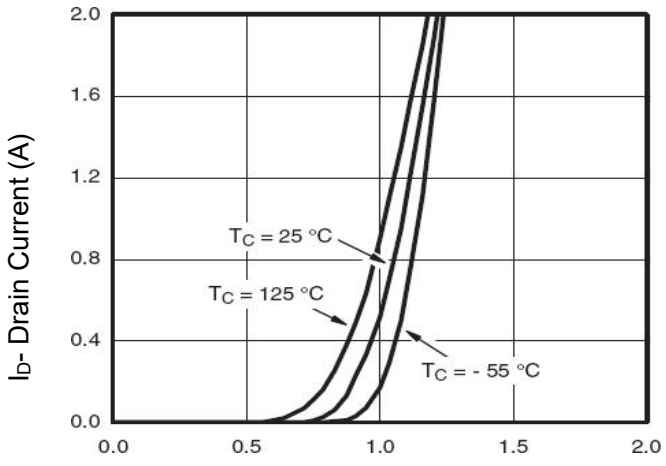


Figure 7 Transfer Characteristics

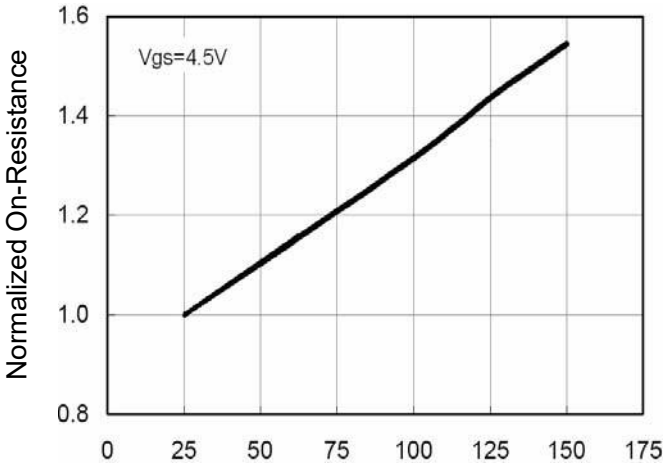


Figure 8 Drain-Source On-Resistance

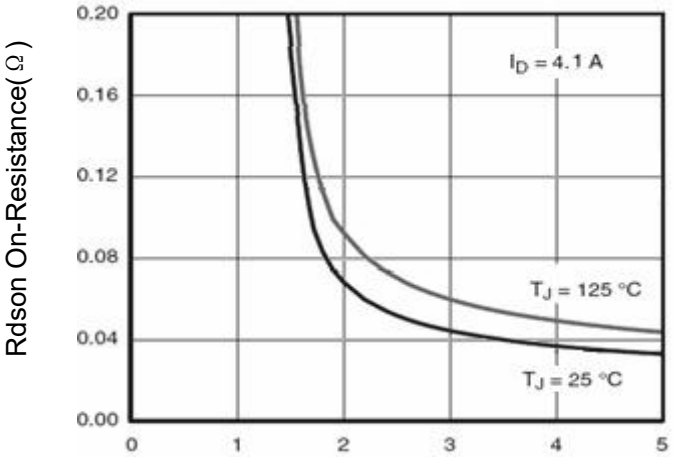


Figure 9 Rdson vs Vgs

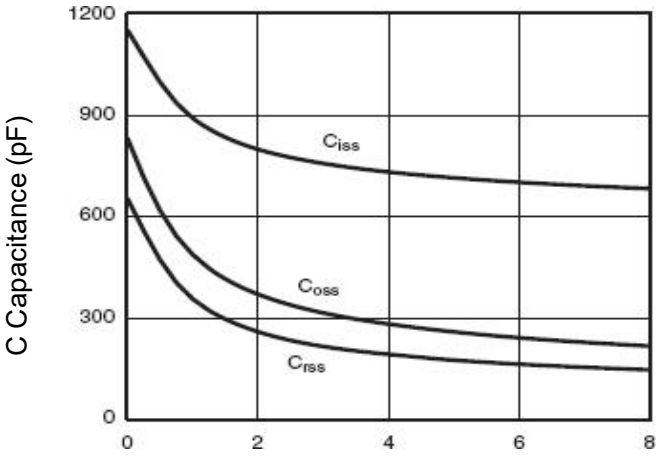


Figure 10 Capacitance vs Vds

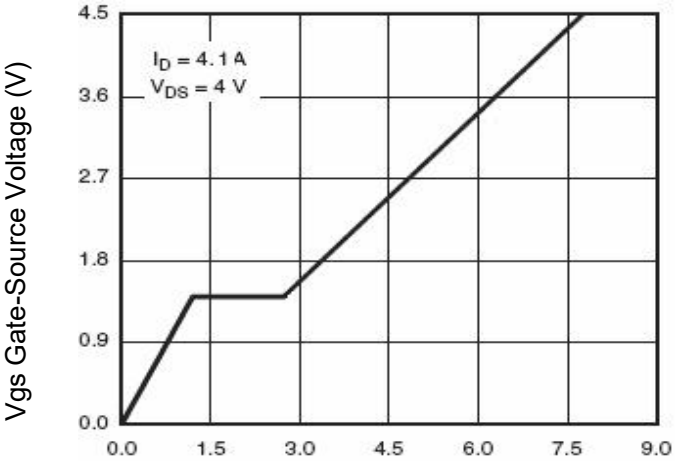


Figure 11 Gate Charge

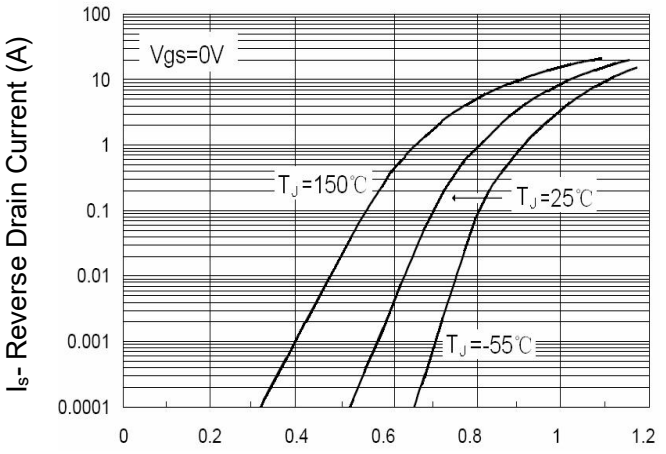
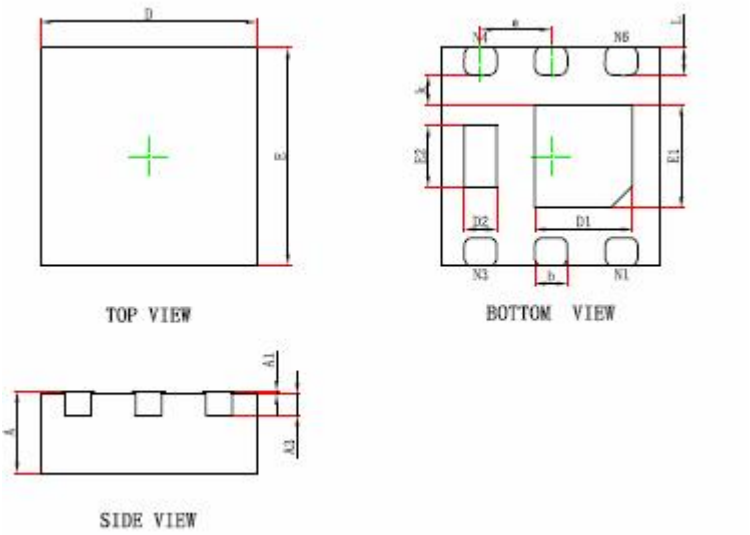


Figure 12 Source- Drain Diode Forward

DFN2X2-6L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.700	0.800	0.028	0.031
A1	0.000	0.050	0.000	0.002
A3	0.203REF.		0.008REF.	
D	1.924	2.076	0.076	0.082
E	1.924	2.076	0.076	0.082
D1	0.800	1.000	0.031	0.039
E1	0.850	1.050	0.033	0.041
D2	0.200	0.400	0.008	0.016
E2	0.460	0.660	0.018	0.026
k	0.200MIN.		0.008MIN.	
b	0.250	0.350	0.010	0.014
e	0.650TYP.		0.026TYP.	
L	0.174	0.326	0.007	0.013